

ABSTRACT

A ferroelectric capacitor including a bottom electrode which has a projecting portion, a top electrode, a ferroelectric layer and a dielectric layer formed between the bottom electrode and the top electrode. The dielectric layer is formed on a peripheral area of the bottom electrode. The ferroelectric layer is formed on the dielectric layer and on the projecting portion of the bottom electrode. As a result, a damaged layer which is formed during an etching process occurs at the ineffective area of the ferroelectric capacitor.